

SANYO	No.1609D	2SC3591
		NPN Epitaxial Planar Silicon Transistor High-Definition CRT Display Horizontal Deflection Output Applications

Features

- Fast switching speed.
- Low saturation voltage.
- Adoption of MBIT process.

Absolute Maximum Ratings at Ta = 25°C

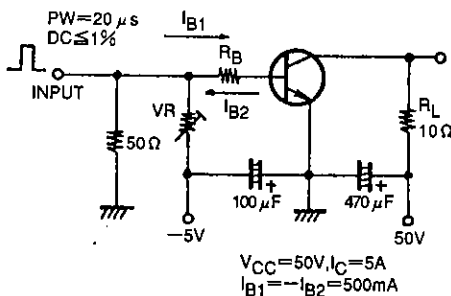
			unit
Collector-to-Base Voltage	V _{CB0}	400	V
Collector-to-Emitter Voltage	V _{CEO}	200	V
Emitter-to-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	7	A
Collector Current (Pulse)	I _{CP}	12	A
Base Current	I _B	4	A
Collector Dissipation	P _C	50	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

T_c = 25°C

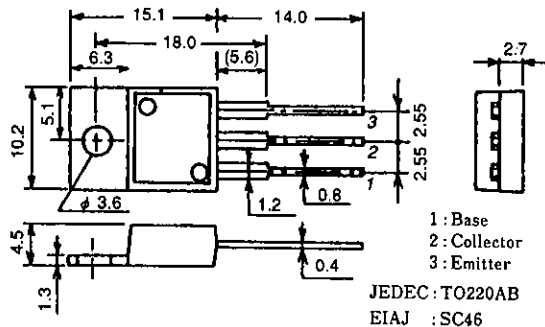
Electrical Characteristics at Ta = 25°C

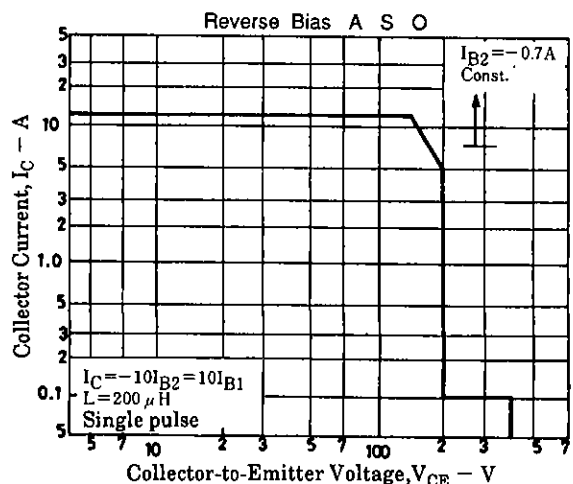
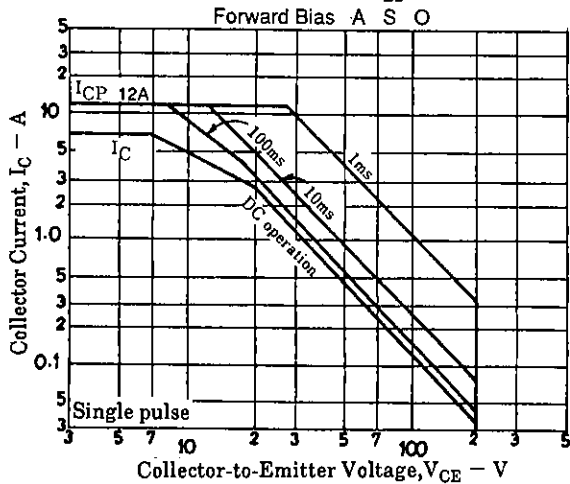
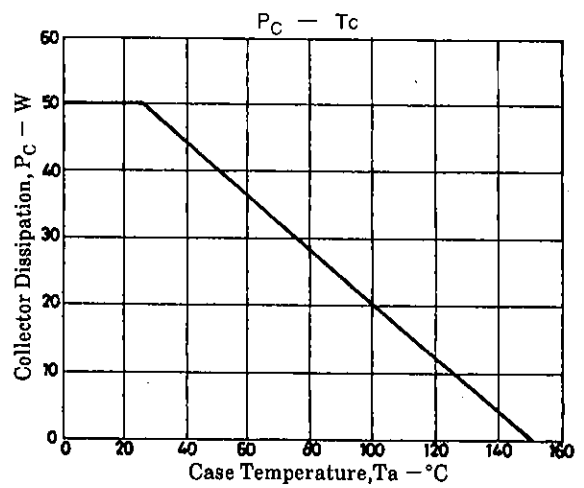
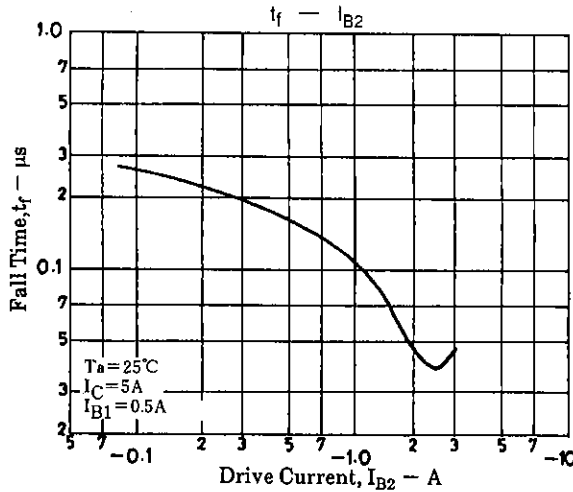
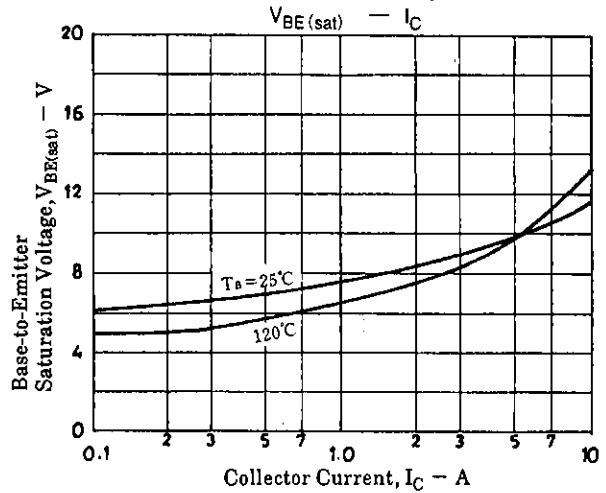
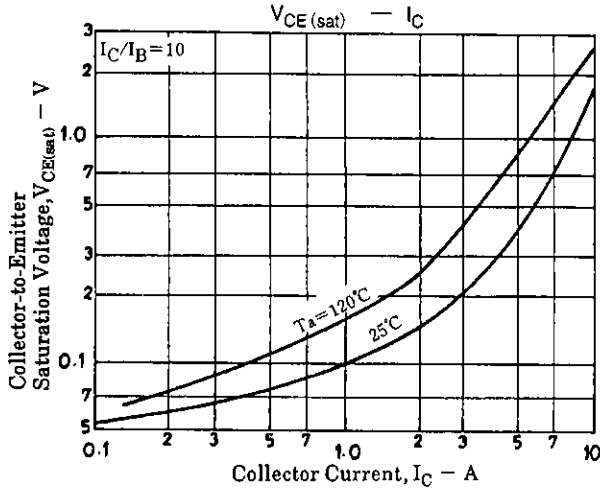
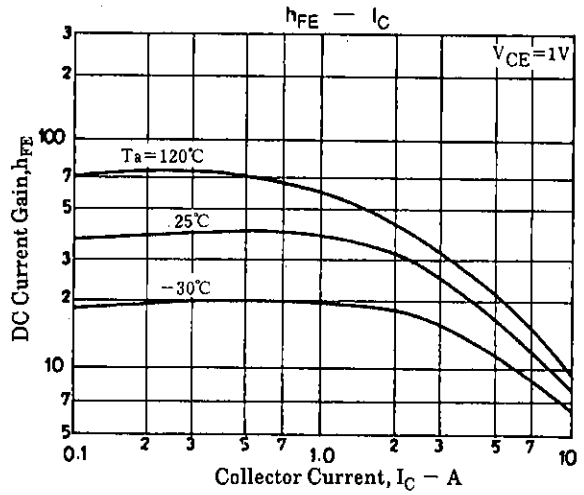
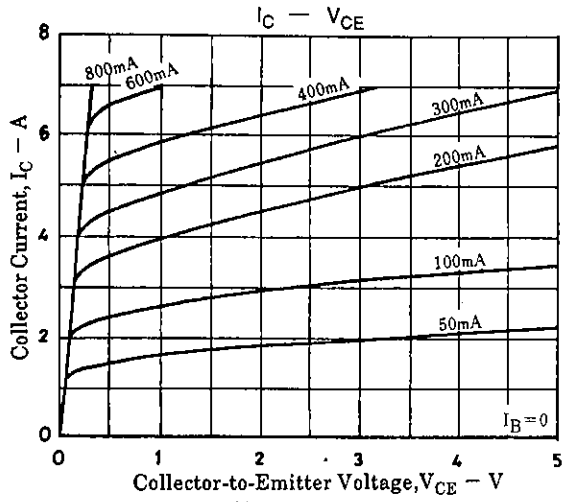
			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} = 250V, I _E = 0			100	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V, I _C = 0			100	μA
DC Current Gain	h _{FE} (1)	V _{CE} = 1V, I _C = 1A	15			
	h _{FE} (2)	V _{CE} = 1V, I _C = 5A	10	50		
Gain-Bandwidth Product	f _T	V _{CE} = 10V, I _C = 0.5A	10	40		MHz
C-E Saturation Voltage	V _{CE(sat)}	I _C = 5A, I _B = 0.5A			0.8	V
B-E Saturation Voltage	V _{BE(sat)}	I _C = 5A, I _B = 0.5A			1.5	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = 1A, I _E = 0	400			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	200			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = 1mA, I _C = 0	6			V
Fall Time	t _f	See specified Test Circuit. I _C = 5A, I _{B1} = -I _{B2} = 0.5A			0.3	μs

Specified Test Circuit



Package Dimensions 2010C
(unit : mm)





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